2SA683

Rev.E Mar.-2016

DATA SHEET

/ Descriptions

WR0<50P ṂṂ ㇾ SQS ᴁṀ ɥ s Ⅱ ㇵ Silicon PNP transistor in a TO-92LM Plastic Package.

/ Features

љ 5VF46;6 Йͅ ´

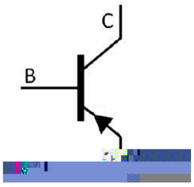
Complementary pair with 2SC1383.

/ Applications

[illegible]

AF power amplifier and driver.

/ Equivalent Circuit



/ Pinning

PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

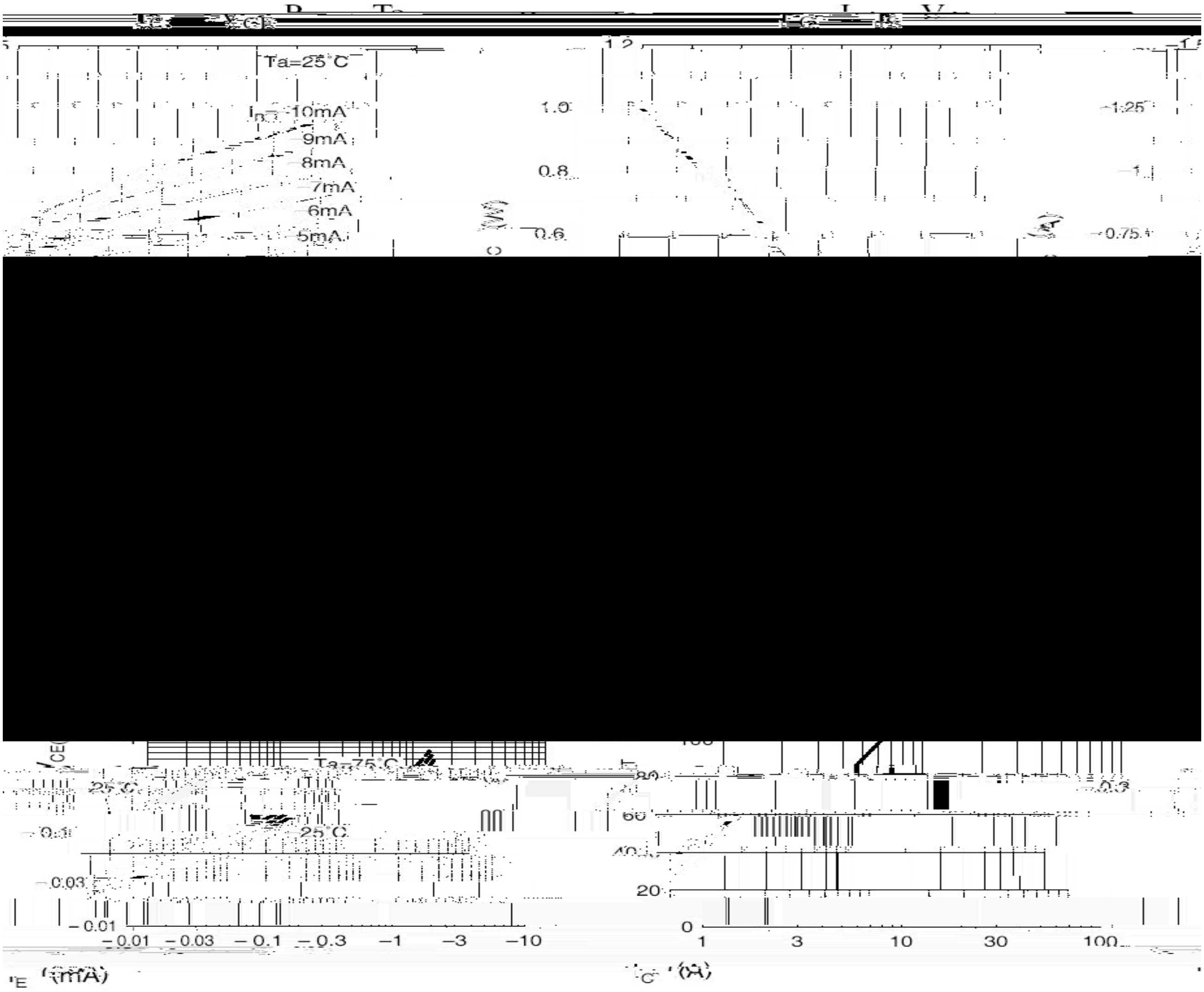
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R	S
h_{FE} Range	85~170	120~240	170~340

v ῼ Parameter	ɣ ᴺ Symbol	ῼ Ѳ Rating	ᴅ ʯ Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-1.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

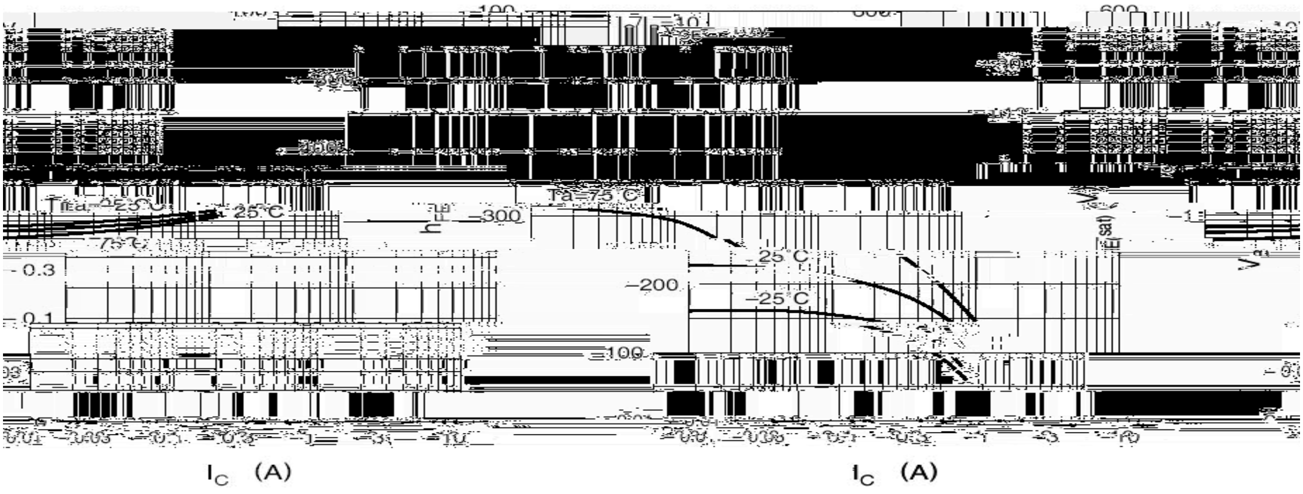
v ῼ Parameter	ɣ ᴺ Symbol	╜ ꜝᶦ ʈ Test Conditions	ῳ ṇ Ѳ Min	Ɛ ʒ Ѳ Typ	ῳ ᶻ Ѳ Max	ᴅ ʯ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10 A I_E=0	-30			V

/ Electrical Characteristic Curve



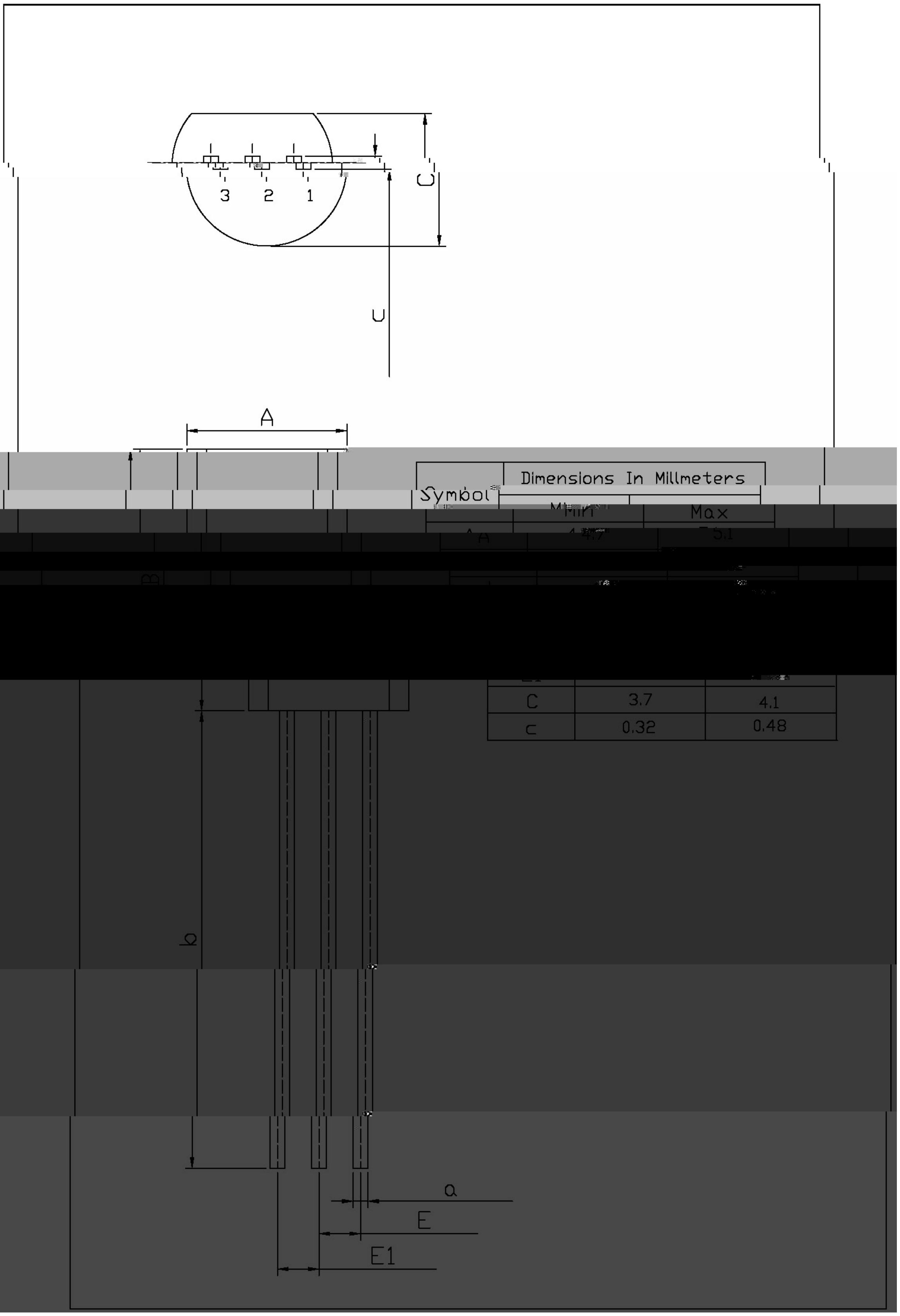
h_{FE} — I_C

$V_{BE(sat)}$ — I_C



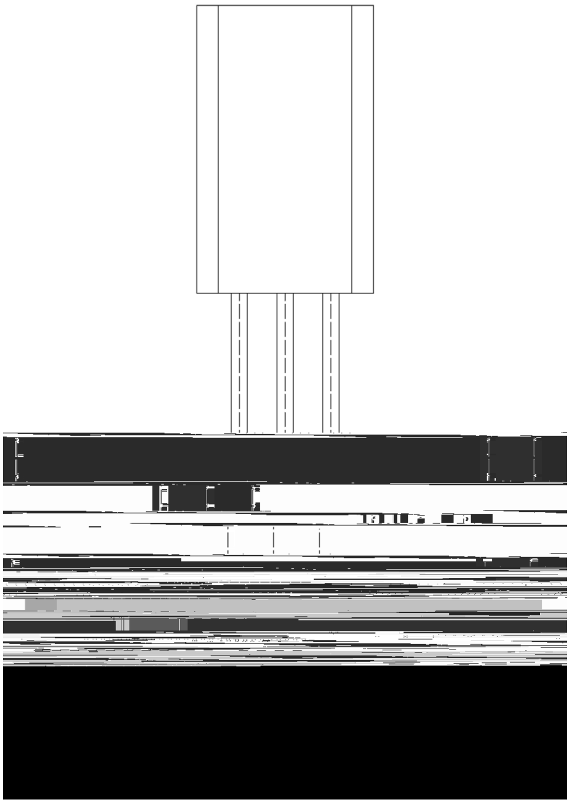
/ Package Dimensions

TO-92LM Unit: mm



Symbol	Dimensions In Millmeters	
	Min	Max
A	4.7	5.1
[illegible]	[illegible]	[illegible]
E1	[illegible]	[illegible]
C	3.7	4.1
c	0.32	0.48

/ Marking Instructions



ب ˝ χ

EU꞉ Ѭ ३ ᴎ Ҧ

D9 ; 6 χ Ѭ ʒ ᴺ Ҧ

T꞉

(   ) / Temperature Profile for Dip Soldering(Pb-Free)

ب ˝ χ	Note:
1 ỉ ♬ □ ŷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;	1.Preheating:25~150 ł , Time:60~90sec.
2 Š Ө □ ŷ 255 ° 5 ł ı `H ڑ `Y ㅐ 㵘 5 ° 0.5sec;	2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.
3 ì ˙ 㐅 ˛ ɔ ฿ ŷ 㵘 2 Ḱ 10 ł /sec.	3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ŷ χ 270 ° 5 ł   `H ڑ χ 10 ° 1 sec.   Temp.:270 ° 5 ł   Time:10 ° 1 sec

/ Packaging SPEC.

ʿΏ ʈ ɣ ŀ / BULK

Package Type	Units	Dimension	(unit mm3)